



# 3

Sheet 1 of 1

<b>FORM PTO-1449</b>		Atty. Docket No.: SAM435-800/01580	Serial No.: 09/903,280
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant:	
		DONG-IL CHO	
		Filing Date	Group Art: 2856
		07/11/01	UNKNOWN

### U.S. PATENT DOCUMENTS

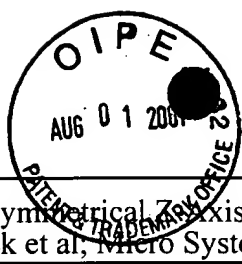
Examiner Initial	Document No.	Date	Name	Class	Sub Class	Filing Date If Appropriate
✓	AA	5616514	04/01/97	Muchow et al.	438	50
✓	AB	5563343	10/08/96	Shaw et al.	73	514.18
✓	AC	5198390	03/30/93	MacDonald et al.	437	203
✓	AD	5930595	07/27/99	Sridhar et al.	438	52

### FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Class	Sub Class	Translation Yes No
AE						

### OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

✓	AF	"Silicon Monolithic Micromechanical Gyroscope," P. Greiff et al. The Charles Stark Draper Laboratory, Cambridge, Mass., 1991.
✓	AG	"Surface Micromachined Z-Axis Vibratory Rate Gyroscope," Clark et al, Berkeley, Calif., June 1996.
✓	AH	"SCREAM I: A Single Mask, Single-Crystal Silicon, Reactive Ion Etching Process For Microelectromechanical Structures," Shaw et al., School of Electrical Engineering and the National Nanofabrication Facility, Cornell University, Ithaca, NY. Sensors and Actuators, 1994, pp. 63-70.
✓	AI	"SOI (SIMOX) As A Substrate For Surface Micromachining Of Single Crystalline Silicon Sensors and Actuators," Diem et al; June 1993, pp. 233-236.
✓	AJ	"A New Silicon Rate Gyroscope," Geiger et al, Hahn-Schickard-Gesellschaft, Institute of Micromachining and Information Technology, Feb. 1998, pp. 615-620.
✓	AK	"Lateral Gyroscope Suspended By Two Gimbals Through High Aspect Ratio ICP Etching," Park et al, Opto-Mechatronics Research, R&D Center, Suwon, Korea, June 1999, pp. 973-975.



<input checked="" type="checkbox"/>	AL	"A Symmetrical Z-Axis Gyroscope With A High Aspect Ratio Using Simple and New Process;" Back et al; Micro Systems, Lab, Samsung Advanced Institute of Technology, Suwon, Korea, Jan 1999.
<input checked="" type="checkbox"/>	AM	"A New Micromachining Technique With (111) Silicon;" Lee et al; School of Electrical Engineering, Seoul National University, Seoul, Korea Jpn. J. Appl. Phys., May 1999, pp. 2699-2703.
<input checked="" type="checkbox"/>	AN	"Mesa-Supported, Single-Crystal Microstructures Fabricated By The Surface/Bulk Micromachining Process;" Park et al; School of Electrical Engineering, Seoul National University, Seoul, Korea Jpn. J. Appl. Phys., July 1999, pp. 4244-4249.
<input checked="" type="checkbox"/>	AO	"The Surface/Bulk Micromachining (SBM) Process: A New Method For Fabricating Released MEMS In Single Crystal Silicon;" Lee et al; J. Microelectromech. Sys., December 1999, pp. 409-416.
<input checked="" type="checkbox"/>	AP	"Surface/Bulk Micromachining (SBM) Process and Deep Trench Oxide Isolation Method For MEMS;" Lee et al; School of Electrical Engineering, College of Engineering, Seoul National University, Seoul, Korea Dec. 1999 pp. 701-704.
<input checked="" type="checkbox"/>	AQ	"Vertical Mirrors Fabricated By Deep Reactive Ion Etching For Fiber-Optic Switching Applications;" Marxer et al; J. Microelectromech. Sys., Sept. 1997, pp. 277-285.
<input checked="" type="checkbox"/>	AR	"Trench Oxide Isolated Single Crystal Silicon Micromachined Accelerometer;" Sridhar et al; Institute of Microelectronics, Singapore; Dec. 1998 pp. 475-478
EXAMINER: John Chapman		DATE CONSIDERED: 10/9/02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.